

PROCESSES FOR FORMING COMPOSITE STRUCTURES WITH A TWO-
DIMENSIONAL MATERIAL USING A POROUS, NON-SACRIFICIAL SUPPORTING
LAYER

CROSS-REFERENCE TO RELATED APPLICATIONS

- 5 [0001] This application claims the benefit of priority under 35 U.S.C. § 119 from United States Provisional Patent Application 61/934,537, filed January 31, 2014, which is incorporated herein by reference in its entirety.

STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH OR
DEVELOPMENT

- 10 [0002] Not applicable.

FIELD

[0003] The present disclosure generally relates to atomically thin films, and, more specifically, to processes for manipulating graphene, graphene-based materials and other two-dimensional materials.

15 BACKGROUND

- [0004] Graphene represents an atomically thin layer of carbon in which the carbon atoms reside within a single sheet or a few stacked sheets (*e.g.*, about 20 or less) of fused six-membered rings forming an extended planar lattice of interconnected hexagonal molecules, although the planar lattice need not necessarily contain six-membered rings exclusively. In this context, graphene represents a planar arrangement of sp^2 - and sp -hybridized carbon atoms that may or may not exhibit a long range crystalline order. In its various forms, graphene has garnered widespread interest for use in a number of applications, primarily due to its favorable combination of high electrical and thermal conductivity values, good in-plane mechanical strength, and unique optical and electronic properties. In many aspects, the properties of graphene parallel those of carbon nanotubes, since both nanomaterials are based upon an extended and electrically conjugated carbon framework. Other two-dimensional materials having an extended planar structure are also of interest for various applications. As
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used herein, the term "two-dimensional material" will refer to any extended planar structure of atomic thickness, including both single- and multi-layer variants thereof. Multi-layer two-dimensional materials can include up to about 20 stacked layers.

[0005] Because of its extended planar structure, graphene offers several features that are not shared with carbon nanotubes. Of particular interest to industry are large-area graphene films for applications such as, for example, special barrier layers, coatings, large area conductive elements (*e.g.*, RF radiators or antennas), integrated circuits, transparent electrodes, solar cells, gas barriers, flexible electronics and the like. In addition, graphene films can be produced in bulk much more inexpensively at the present time than can carbon nanotubes.

[0006] Large-area graphene films of atomic thicknesses and containing single- or multi-layer graphene can be produced by a variety of chemical vapor deposition (CVD) processes. CVD growth takes place on a metal-containing growth substrate, such as a copper or nickel foil, and the graphene is strongly adhered to the growth substrate following synthesis. Even the outer graphene layers in multi-layer graphene, which are spatially separated from the surface of the growth substrate, can remain strongly adhered to the growth substrate. The strong adherence of graphene to its growth substrate can make intact removal of the graphene film difficult.

[0007] Metal growth substrates are often undesirable for use in downstream applications utilizing a graphene film. For example, chemical, electrical, or functional incompatibility can result when attempting to utilize a graphene film that is still adhered to or in contact with its metal growth substrate. Accordingly, it can often be desirable to transfer a graphene film from its metal growth substrate onto a secondary substrate, also referred to herein as a "functional substrate" or a "receiving substrate." The secondary substrate can exhibit properties that are better suited to meet the needs of a particular application.

[0008] Removing a graphene film from its growth substrate and subsequently transferring the graphene film to a secondary substrate can be difficult for a number of reasons. Although graphene has high mechanical strength on an atomic basis, it can be fairly fragile on the macroscale once it has been removed from its growth substrate. For example, tearing, fracturing and/or buckling can occur in the process of liberating a graphene film from

its growth substrate. Tearing and buckling can produce poor surface conformality and coverage upon transferring the graphene film to a secondary substrate. Some processes for affecting removal of a graphene film from its growth substrate can also produce undesirable chemical damage to the graphene film, which can degrade its desirable properties.

5 [0009] One solution for addressing the difficulties posed by unsupported graphene films involves depositing a supporting layer on the graphene film that temporarily provides mechanical stabilization during the transfer process. Poly(methyl methacrylate) (PMMA) layers have been used in this regard. Once transfer to the secondary substrate is complete, the supporting layer is removed from the graphene film, meaning that the supporting layer is
10 sacrificial and does not remain associated with the graphene film in its end deployment configuration. The use of a sacrificial supporting layer to promote transfer of graphene films can be undesirable for a number of reasons including, for example, incomplete layer removal following transfer, chemical damage to the graphene film and/or the secondary substrate during the layer removal process, poor surface conformality of the graphene film to the
15 secondary substrate due to constraintment by the supporting layer, and potential incursion of the supporting layer into perforations within the graphene film. Chemicals used to affect removal of the sacrificial supporting layer can often be particularly incompatible with the polymer materials forming the secondary substrate. Further, the additional processing operations needed to deposit and then remove the sacrificial supporting layer can be
20 undesirable from a time and cost standpoint.

[0010] In view of the foregoing, facile techniques for manipulating graphene films without using a sacrificial supporting layer would be of considerable benefit in the art. The present disclosure satisfies the foregoing need and provides related advantages as well.

SUMMARY

25 [0011] In various embodiments, processes for manipulating a two-dimensional material are described herein. In some embodiments, the processes can include providing a two-dimensional material adhered to a growth substrate, depositing a supporting layer on the two-dimensional material while the two-dimensional material is adhered to the growth substrate, and releasing the two-dimensional material from the growth substrate. The two-
30 dimensional material remains in contact with the supporting layer following release of the

two-dimensional material from the growth substrate.

[0012] In some embodiments, processes of the present disclosure can include providing a graphene or graphene-based film adhered to a growth substrate, perforating the film to introduce a plurality of pores therein, depositing a supporting layer on the film while the film is adhered to the growth substrate, and releasing the graphene or graphene-based film from the growth substrate. The graphene or graphene-based film remains in contact with the supporting layer following release of the film from the growth substrate. In some embodiments, the growth substrate includes a metal, and the supporting layer includes a plurality of pores.

[0013] In other embodiments, filtration membranes containing a perforated graphene or graphene-based material film and a supporting layer are described herein. The filtration membranes are prepared by a process that includes: providing a graphene or graphene-based film adhered to a growth substrate, perforating the film to introduce a plurality of pores therein, depositing a supporting layer on the film while the film is adhered to the growth substrate, and releasing the film from the growth substrate. The graphene or graphene-based film remains in contact with the supporting layer following release of the film from the growth substrate. In some embodiments, the growth substrate includes a metal, and the supporting layer includes a plurality of pores.

[0014] The foregoing has outlined rather broadly the features of the present disclosure in order that the detailed description that follows can be better understood. Additional features and advantages of the disclosure will be described hereinafter. These and other advantages and features will become more apparent from the description below taken in conjunction with the drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0015] For a more complete understanding of the present disclosure, and the advantages thereof, reference is now made to the following descriptions to be taken in conjunction with the accompanying drawings describing specific embodiments of the disclosure, wherein:

[0016] FIGURE 1 shows an illustrative schematic of a graphene or graphene-based

film sandwiched between a growth substrate and a supporting layer;

[0017] FIGURE 2 shows an illustrative schematic of a graphene or graphene-based film in contact with only a supporting layer, following removal of a growth substrate to liberate the graphene or graphene-based film;

5 [0018] FIGURE 3 shows a schematic of an illustrative process whereby a graphene or graphene-based film or other two-dimensional material can be formed on a growth substrate and undergo subsequent removal therefrom in supported form;

[0019] FIGURES 4 and 5 show illustrative processes whereby a graphene or graphene-based film and a porous or permeable supporting layer can be freed from a growth
10 substrate by an etching solution and then undergo contiguous transfer to a secondary substrate; and

[0020] FIGURE 6 shows an illustrative SEM image of a graphene or graphene-based film having a plurality of electrospun PVDF fibers deposited thereon.

[0021] FIGURE 7 shows an illustrative schematic of damage caused by debris
15 disposed between graphene or a graphene-based material and a secondary substrate when (a) graphene or a graphene-based material is applied to an existing secondary substrate and (b) a secondary substrate is applied to graphene or a graphene-based material.

[0022] FIGURE 8 shows an illustrative SEM image of damage to a graphene or graphene-based film caused by debris disposed between the film and an existing secondary
20 substrate, as shown in FIGURE 7(a).

DETAILED DESCRIPTION

[0023] The present disclosure is directed, in part, to methods of forming composite structures comprising a non-sacrificial supporting layer and a graphene, graphene-based or other two-dimensional material. Graphene-based materials include, but are not limited to,
25 single layer graphene, multilayer graphene or interconnected single or multilayer graphene domains and combinations thereof. In embodiments, multilayer graphene includes 2 to 20 layers, 2 to 10 layers or 2 to 5 layers. In embodiments, graphene is the dominant material in a

graphene-based material. For example, a graphene-based material comprises at least 30% graphene, or at least 40% graphene, or at least 50% graphene, or at least 60% graphene, or at least 70% graphene, or at least 80% graphene, or at least 90% graphene, or at least 95% graphene. In embodiments, a graphene-based material comprises a range of graphene
5 selected from 30% to 95%, or from 40% to 80% or from 50% to 70%.

[0024] As used herein, a “domain” refers to a region of a material where atoms are uniformly ordered into a crystal lattice. A domain is uniform within its boundaries, but different from a neighboring region. For example, a single crystalline material has a single domain of ordered atoms. In an embodiment, at least some of the graphene domains are
10 nanocrystals, having domain sizes from 1 to 100 nm or 10-100 nm. In an embodiment, at least some of the graphene domains have a domain size greater than 100 nm up to 100 microns, or from 200 nm to 10 microns, or from 500 nm to 1 micron. “Grain boundaries” formed by crystallographic defects at edges of each domain differentiate between neighboring crystal lattices. In some embodiments, a first crystal lattice may be rotated
15 relative to a neighboring second crystal lattice, by rotation about an axis perpendicular to the plane of a sheet, such that the two lattices differ in “crystal lattice orientation”.

[0025] In an embodiment, the sheet of graphene-based material comprises a sheet of single or multilayer graphene or a combination thereof. In an embodiment, the sheet of graphene-based material is a sheet of single or multilayer graphene or a combination thereof.
20 In another embodiment, the sheet of graphene-based material is a sheet comprising a plurality of interconnected single or multilayer graphene domains. In an embodiment, the interconnected domains are covalently bonded together to form the sheet. When the domains in a sheet differ in crystal lattice orientation, the sheet is polycrystalline.

[0026] In embodiments, the thickness of the sheet of graphene-based material is from
25 0.34 to 10 nm, from 0.34 to 5 nm, or from 0.34 to 3 nm. A sheet of graphene-based material may comprise intrinsic defects. Intrinsic defects are those resulting unintentionally from preparation of the graphene-based material in contrast to perforations which are selectively introduced into a sheet of graphene-based material or a sheet of graphene. Such intrinsic defects include, but are not limited to, lattice anomalies, pores, tears, cracks or wrinkles.
30 Lattice anomalies can include, but are not limited to, carbon rings with other than 6 members

(e.g. 5, 7 or 9 membered rings), vacancies, interstitial defects (including incorporation of non-carbon atoms in the lattice), and grain boundaries.

[0027] In an embodiment, the layer comprising the sheet of graphene-based material further comprises non-graphenic carbon-based material located on the a surface of the sheet of graphene-based material. In an embodiment, the non-graphenic carbon-based material does not possess long-range order and may be classified as amorphous. In embodiments, the non-graphenic carbon-based material further comprises elements other than carbon and/or hydrocarbons. Non-carbon materials which may be incorporated in the non-graphenic carbon-based material include, but are not limited to, hydrogen, hydrocarbons, oxygen, silicon, copper and iron. In embodiments, carbon is the dominant material in non-graphenic carbon-based material. For example, a non-graphenic carbon-based material comprises at least 30% carbon, or at least 40% carbon, or at least 50% carbon, or at least 60% carbon, or at least 70% carbon, or at least 80% carbon, or at least 90% carbon, or at least 95% carbon. In embodiments, a non-graphenic carbon-based material comprises a range of carbon selected from 30% to 95%, or from 40% to 80%, or from 50% to 70%.

[0028] The present disclosure is directed, in part, to processes for removing graphene, graphene-based material and other two-dimensional materials from their growth substrates. The present disclosure is also directed, in part, to processes for manipulating graphene, graphene-based material and other two-dimensional materials that are free of a growth substrate. The present disclosure is also directed, in part, to composite structures and filtration membranes formed from perforated graphene or graphene-based material that has been released from its growth substrate.

[0029] As discussed above, transferring graphene graphene-based material and other two-dimensional materials from a growth substrate to a secondary substrate can be exceedingly complicated. For example, mechanical damage and morphological changes can occur during the transfer process. Surface conformality of the transferred two-dimensional material on the secondary substrate can also be problematic. In this regard, if the secondary substrate is not sufficiently smooth, the transferred two-dimensional material can tear during deposition. The need for sufficient surface smoothness can severely limit candidate material choices for secondary substrates. Although some of the foregoing issues can be mitigated to

a degree by using a sacrificial supporting layer (*e.g.*, PMMA) to promote thin film transfer, sacrificial supporting layers can introduce their own set of problems, as discussed above. In addition, PMMA is not particularly flexible, which can be problematic for facilitating downstream applications.

5 [0030] Many applications for graphene, graphene-based material and other two-dimensional materials have been envisioned based upon the intentional introduction of a plurality of pores of defined size within the planar structure of these entities. As used herein, the term "pore" will refer to an aperture or hole extending through the thickness of graphene, graphene-based material or a similar two-dimensional material. Graphene, graphene-based
10 material and other two-dimensional materials having intentionally introduced pores within their planar structure will be referred to herein as being "perforated," and the action of introducing pores will be referred to as "perforating." In a graphene or graphene-based sheet an interstitial aperture is formed by each six carbon atom ring structure in the sheet and this interstitial aperture is less than one nanometer across. In particular, this interstitial aperture,
15 defined by the center-to-center distance between carbon atoms, is believed to be about 0.3 nanometers across its longest dimension. Perforation of sheets comprising two-dimensional network structures typically refers to formation of holes larger than the interstitial apertures in the network structure. Filtration represents an illustrative application that has been envisioned for perforated graphene, graphene-based material and other perforated two-
20 dimensional materials, since substances of atomic or molecular dimensions can be effectively filtered by utilizing pores having a small enough size. Since graphene, graphene-based material and other two-dimensional materials are so thin, high flux rates can desirably be achieved even with very small pore sizes. This is not the case with filtration membranes having a thicker active filtration layer.

25 [0031] Sacrificial supporting layers can be particularly problematic for use in conjunction with perforated graphene, graphene-based material and other perforated two-dimensional materials, since their difficult removal can affect porosity of the planar structure. Chemical damage and effective sourcing of porous or permeable secondary substrates can also present issues when utilizing a transferred two-dimensional material as an active
30 filtration layer. Moreover, sacrificial supporting layers that have been previously used in the art are believed to lack sufficient porosity to allow their direct use in applications making use

of porosity within graphene, graphene-based material or a similar two-dimensional material.

[0032] The present inventors recognized that instead of using a sacrificial (temporary) supporting layer to promote transfer of graphene, graphene-based material and other two-dimensional materials to a secondary substrate, a non-sacrificial supporting layer can be effectively utilized to facilitate manipulation of these thin film materials in the form of a robust composite structure. As used herein, the term "non-sacrificial" refers to a supporting layer that remains associated with graphene, graphene-based material or another two-dimensional material in the two-dimensional material's terminal deployment. The properties of the non-sacrificial supporting layer can be chosen or tailored for compatibility with the particular terminal deployment. Elimination of a sacrificial supporting layer provides fewer opportunities for damaging the two-dimensional material during processing and benefits in the form of time and material savings. In addition, various non-sacrificial supporting layers can be readily deposited or formed with porosity established therein, which can be particularly useful in combination with perforated two-dimensional materials for filtration and other applications.

[0033] A number of different types of supporting layers, both polymeric and non-polymeric, can be utilized in conjunction with the embodiments of the present disclosure. The particular material utilized in the supporting layer can be chosen based upon the chemical or physical environment into which the graphene, graphene-based material or other two-dimensional material is being terminally deployed. Moreover, a number of processes can be used to deposit the supporting layer, thereby allowing considerable flexibility to be realized in its composition and morphology. Further advantages of such approaches are discussed hereinbelow.

[0034] In some embodiments, a non-sacrificial supporting layer of the present disclosure can be used to promote transfer of graphene, graphene-based material or another two-dimensional material to a secondary substrate. When used in this manner, the two-dimensional material can be sandwiched between the supporting layer and the secondary substrate, or the supporting layer can be sandwiched between the two-dimensional material and the secondary substrate. In either case, the non-sacrificial supporting layer does not significantly compromise the ability of the two-dimensional material to perform its intended

function. For example, in filtration applications, a porous, non-sacrificial supporting layer can allow a perforated two-dimensional material to function as an active filtration layer by allowing free liquid or gas passage to take place upstream and/or downstream of the two-dimensional material. In configurations where the two-dimensional material is sandwiched
5 between the secondary substrate and the supporting layer, the pores within the supporting layer can be effective to pre-filter large particles before they have an opportunity to plug the smaller pores within the two-dimensional material.

[0035] In some embodiments, a number of non-sacrificial supporting layers can be directly deposited in a porous or permeable condition, or porosity can be created within the
10 supporting layer after its deposition on the two-dimensional material. In either case, the porosity within the supporting layer can be of a sufficient magnitude to allow access to the pores within a perforated two-dimensional material on which the supporting layer is deposited. For example, a porous or permeable, non-sacrificial supporting layer deposited on
15 a perforated two-dimensional material can constitute at least a portion of a filtration membrane in various embodiments of the present disclosure. Such filtration membranes can display more consistent filtration properties than similar membranes prepared by transferring the two-dimensional material to a secondary substrate through use of a sacrificial supporting layer.

[0036] Accordingly, the processes described herein allow graphene, graphene-based
20 material and other two-dimensional materials to be used in conjunction with a much broader array of materials than would otherwise be possible. Further, by depositing a polymer or other supporting layer substance directly on a two-dimensional material, better surface coverage and morphological properties can be attained than by performing the reverse and conventional process of depositing a previously synthesized two-dimensional material onto
25 an existing substrate. The processes of the present disclosure allow for improved physical and chemical interactions to take place between the two-dimensional material and the supporting layer. In addition, a direct deposit approach may decrease or prevent delamination of the two-dimensional material and supporting layer by improving adhesion between the layers. As an additional advantage, direct deposition approaches of the present
30 disclosure can decrease the likelihood of trapping debris between the two-dimensional material and the supporting layer, or mitigate damage caused by trapped debris.

[0037] FIGURE 7 shows an illustrative schematic of damage caused by debris disposed between graphene or a graphene-based material and a secondary substrate when (a) graphene or a graphene-based material is applied to an existing secondary substrate and (b) a secondary substrate is applied to graphene or a graphene-based material. When graphene or a graphene-based material is applied to an existing substrate pressure is typically applied to encourage contact of the film and substrate. Such pressure may allow debris to break through the film, thereby creating damage of the type shown in FIGURE 8, which shows an illustrative SEM image of damage to a graphene or graphene-based film caused by debris disposed between the film and an existing secondary substrate. In contrast, methods disclosed herein apply a secondary substrate to an existing graphene or graphene-based material. The secondary substrate is typically applied via a solution technique, a vapor deposition technique, an electrospinning technique or another technique that allows the secondary substrate to at least partially encapsulate any debris particles present on the graphene or graphene-based material.

[0038] Although the processes described herein can be particularly advantageous for use in conjunction with perforated two-dimensional materials, it is to be recognized that some or all of these advantages can also be recognized whether the two-dimensional material is perforated or not. For example, enhanced surface coverage and conformality on the supporting layers of the present disclosure can still be realized even if the two-dimensional material is not perforated. Moreover, the features and advantages of the present disclosure can be realized with non-sacrificial supporting layers that are either porous, permeable or substantially non-porous or permeable. Furthermore, although certain embodiments are described herein with graphene or graphene-based material as the two-dimensional material, it is to be recognized that other two-dimensional materials can be used similarly in alternative embodiments of the present disclosure unless otherwise specified herein. Thus, considerable flexibility can be realized by practicing the disclosure herein.

[0039] In various embodiments, processes for removing a two-dimensional material, such as graphene or graphene-based material, from its growth substrate can include: providing a two-dimensional material adhered to a growth substrate, depositing a supporting layer on the two-dimensional material while the two-dimensional material is adhered to the growth substrate, and releasing the two-dimensional material from the growth substrate. The

two-dimensional material remains in contact with the supporting layer following release of the two-dimensional material from the growth substrate. The combination of the two-dimensional material in contact with the supporting layer defines a composite structure.

[0040] The two-dimensional material can be any substance having an extended planar molecular structure and an atomic level thickness. Particular examples of two-dimensional materials include graphene films, graphene-based material, transition metal dichalcogenides, α -boron nitride, silicene or germanene or other materials having a like planar structure. Specific examples of transition metal dichalcogenides include molybdenum disulfide and niobium diselenide. Graphene or graphene-based films according to the embodiments of the present disclosure can include single-layer or multi-layer films, or any combination thereof. Choice of a suitable two-dimensional material can be determined by a number of factors, including the chemical and physical environment into which the graphene, graphene-based material or other two-dimensional material is to be terminally deployed, ease of perforating the two-dimensional material, and the like.

[0041] FIGURE 1 shows an illustrative schematic of a graphene or graphene-based film sandwiched between a growth substrate and a supporting layer. As depicted in FIGURE 1, graphene or graphene-based film 4 is present on its original growth substrate 2. Graphene or graphene-based film 4 can be perforated or unperforated depending on the intended terminal deployment for the graphene or graphene-based film. Upon graphene or graphene-based film 4 is deposited supporting layer 6, such that graphene or graphene-based film 4 is sandwiched between growth substrate 2 and supporting layer 6. Supporting layer 6 can be porous, permeable or substantially non-porous or impermeable, depending on its intended function, as well as the intended function of the graphene or graphene-based film.

[0042] FIGURE 2 shows an illustrative schematic of graphene or graphene-based film 4 in contact with only supporting layer 6, following removal of growth substrate 2 to liberate graphene or graphene-based film 4. A high degree of surface conformality is established between graphene or graphene-based film 4 and supporting layer 6, thereby maintaining mechanical support of graphene or graphene-based film 4. Although FIGURE 2 has depicted complete removal of growth substrate 2, it is to be recognized that complete removal of growth substrate 2 need not necessarily take place. Instead, only a sufficient amount of

removal of growth substrate 2 needs to take place to affect release of graphene film 4 and supporting layer 6 to produce the configuration depicted in FIGURE 2. Removal of growth substrate 2 can involve etching the growth substrate with an etching solution. In alternative configurations, graphene or graphene-based film 4 and supporting layer 6 can be delaminated from growth substrate 2 in order to leave growth substrate 2 intact.

[0043] FIGURE 3 shows a schematic of an illustrative process whereby a graphene or graphene-based film or other two-dimensional material can be formed on a growth substrate and undergo subsequent removal therefrom in supported form. As depicted in FIGURE 3, graphene or graphene-based film 4 is deposited on growth substrate 2 during operation 10. Thereafter, in operation 20, supporting layer 6 is deposited on graphene or graphene-based film 4 while graphene or graphene-based film 4 is still present on growth substrate 2. Suitable techniques for forming, casting or depositing supporting layer 6 onto graphene or graphene-based film 4 are discussed in greater detail hereinbelow. Additional operations for introducing pores into graphene or graphene-based film 4 or supporting layer 6 are also discussed in further detail hereinbelow. Finally, in operation 30, growth substrate 2 is removed or released, leaving behind graphene or graphene-based film 4 supported by supporting layer 6, thereby defining composite structure 32.

[0044] In more particular embodiments, the growth substrate can include a metal. Various metals, particularly transition metals, can be effective for promoting growth of a two-dimensional material thereon. For example, in the case of graphene or graphene-based films, a copper substrate or a nickel substrate can be particularly effective as a growth substrate. In some embodiments, the growth substrate can be formed substantially entirely of a metal, such as a metal foil. In other embodiments, the growth substrate can include a metal surface. For example, a ceramic substrate having a metal surface coating can be used as the growth substrate in various embodiments of the present disclosure.

[0045] In various embodiments, releasing the graphene or graphene-based film or other two-dimensional material from the growth substrate can involve etching the growth substrate. In various embodiments, the operation of etching the growth substrate to affect release of the graphene or graphene-based film or other two-dimensional material can involve a dissolution process. Accordingly, the etching operation can include exposing at least the

growth substrate to an etching solution. A particularly suitable etching solution for metal growth substrates, particularly copper and other transition metals, can include ammonium persulfate as the active etching component. That is, in some embodiments, etching the growth substrate can involve at least partially dissolving a metal with an ammonium persulfate etch solution. Other oxidizing etchants can also be suitable for at least partially dissolving a metal substrate according to the embodiments of the present disclosure. Illustrative examples of other suitable etchants can include etching solutions containing, for example, ferric salts (e.g., ferric chloride), cupric salts, potassium peroxydisulfate, hydrogen peroxide-ammonia, peroxide, hydrochloric acid, acetic acid, hydrofluoric acid, nitric acid and combinations thereof. In addition, electrochemical etching may be used to release graphene, graphene-based materials or other two-dimensional materials from a metallic growth substrate.

[0046] In alternative embodiments, releasing the graphene or graphene-based film or other two-dimensional material from the growth substrate can involve delaminating the graphene or graphene-based film or other two-dimensional material from the growth substrate. Illustrative delamination processes can involve, for example, electrolytic generation of hydrogen gas between the graphene or graphene-based film and the growth substrate to promote delamination.

[0047] In some embodiments, a supporting layer and a graphene or graphene-based film or other two-dimensional material can be used without another secondary substrate being present. In other instances, however, it can still be desirable to transfer the supporting layer and the graphene or graphene-based film or other two-dimensional material to a secondary substrate. In some embodiments, both the removal and transfer processes can be promoted by an etching solution and optionally another liquid. FIGURE 4 shows an illustrative process whereby a graphene or graphene-based film and porous or permeable supporting layer can be freed from a growth substrate by an etching solution and then undergo transfer to a secondary substrate. As depicted in FIGURE 4, etching solution 50 is provided in etching tank 52. Growth substrate 2 is placed in contact with etching solution 50. Adhered graphene or graphene-based film 4 and supporting layer 6 can also contact etching solution 50 in some embodiments. In some embodiments, growth substrate 2 and its adhered layer(s) can float on the surface of etching solution 50 by native buoyancy alone. In other embodiments, a high

buoyancy material, such as a foam, can be utilized in order to promote floatation of growth substrate 2 and its adhered layer(s) on etching solution 50. The high buoyancy material can also surround growth substrate 2 so as to limit the lateral movement of graphene or graphene-based film 4 once it has been removed from growth substrate 2. As etching solution 50 affects dissolution of growth substrate 2 during operation 60, graphene or graphene-based film 4 and supporting layer 6 remain floating on etching solution 50. Thereafter, the level of etching solution 50 in etching tank 52 can be lowered to settle graphene or graphene-based film 4 and supporting layer 6 onto secondary substrate 8, as shown in operation 70. Optionally, graphene or graphene-based film 4 and supporting layer 6 can be floated to a different liquid phase lacking the active etchant (*e.g.*, water or a water-alcohol mixture), and they can be lowered onto secondary substrate 8 in a substantially equivalent manner. Once deposited on secondary substrate 8, graphene or graphene-based film 4 can be removed and utilized in various applications. Similar processes can be used to manipulate graphene or graphene-based film 4 and supporting layer 6 produced by mechanical delamination.

[0048] In FIGURE 4, graphene or graphene-based film 4 is sandwiched between secondary substrate 8 and supporting layer 6. FIGURE 5 shows a schematic of an alternative configuration in which supporting layer 6 directly contacts secondary substrate 8, with graphene or graphene-based film 4 being directed outwardly. The operations used to produce the configuration of FIGURE 5 are substantially similar to those described above for FIGURE 4, but they are performed on an inverted or flipped stack, *i.e.*, where supporting layer 6 is below the two-dimensional material when viewed in cross-section. The stack may be inverted or flipped prior to release of the growth substrate or after release of the growth substrate. When the stack is inverted or flipped after release of the growth substrate, the two-dimensional material remains sufficiently supported by supporting layer 6 during the inverting or flipping operation to prevent tearing, folding or other damage to the two-dimensional material.

[0049] Accordingly, in some embodiments, processes of the present disclosure can include transferring the graphene, graphene-based material or other two-dimensional material to a secondary substrate. When used, the secondary substrate can also be porous or permeable. For example, when constructing a filtration membrane containing a perforated graphene or graphene-based film and a porous or permeable supporting layer, the secondary

substrate can also be porous or permeable in order to allow fluid flow to freely take place within the stacked structure.

[0050] It is believed that any material can be used to form the secondary substrate or the supporting layer, provided that the chosen material suitably adheres to the graphene or graphene-based film or other two-dimensional material. Adhesion between the graphene or graphene-based film and/or layers of the stacked structure may be facilitated by a high degree of conformality between the layers, where the conformal contact between the layers may improve van der Waals forces, dielectric forces, covalent bonding and/or ionic bonding. The ability to generate suitable porosity in the secondary substrate and/or the supporting layer can also dictate the suitability of a particular material. Illustrative materials can include, for example, various polymers, ceramics, carbon grids, and the like.

[0051] As indicated above, the secondary substrate can desirably be omitted in various embodiments of the present disclosure. That is, a graphene or graphene-based film and its adhered supporting layer can be terminally deployed in various applications. Accordingly, when a graphene or graphene-based film and its adhered supporting layer are to be used without a secondary substrate being present, transferring operations can be omitted (*e.g.*, operation 60 in FIGURES 4 and 5).

[0052] In various embodiments, the supporting layer of the present disclosure can have a plurality of pores therein. In some embodiments, the plurality of pores in the supporting layer can be natively introduced as the supporting layer is deposited on the graphene, graphene-based material or other two-dimensional material. In other embodiments, the plurality of pores in the supporting layer can be introduced separately after the supporting layer is deposited. In either case, processes of the present disclosure can include introducing a plurality of pores into the supporting layer. Suitable techniques for depositing or forming a porous or permeable supporting layer are discussed in greater detail hereinbelow.

[0053] In some embodiments, the supporting layer can have a "pore size gradient" throughout its thickness. "Pore size gradient", as used herein, describes a plurality of pores in a supporting layer having a diameter of each pore that increases or decreases along an imaginary line through the center of the pore. For example, a supporting layer may have a

pore size gradient that decreases or narrows nearer the surface of a two-dimensional material or along a direction of fluid or gas flow. In such an embodiment, a pore size of the supporting layer is smaller nearer the surface of a two-dimensional material than at an opposite side of the supporting layer.

5 [0054] In some embodiments, the supporting layer can have a "porosity gradient" throughout its thickness. "Porosity gradient", as used herein, describes a change, along a dimension of the supporting layer, in the "porosity" or ratio of the volume of all pores in a layer to the volume of the whole layer. For example, throughout the thickness of the porous supporting layer, the porosity can change in a regular or irregular manner. Generally, a
10 porosity gradient decreases from one face of the supporting layer to the other. For example, the lowest porosity in the supporting layer can be located spatially closest to the graphene or graphene-based film or other two-dimensional material, and the highest porosity can be located farther away. A porosity gradient of this type may be achieved by electrospinning
15 two-dimensional material and less dense further from the surface of the two-dimensional material.

[0055] In some embodiments, the supporting layer can have a "permeability gradient" throughout its thickness. "Permeability gradient", as used herein, describes a change, along a dimension of the supporting layer, in the "permeability" or rate of flow of a liquid or gas
20 through a porous material. For example, throughout the thickness of the supporting layer, the permeability can change in a regular or irregular manner. Generally, a permeability gradient decreases from one face of the supporting layer to the other. For example, the lowest permeability in the supporting layer can be located spatially closest to the graphene or graphene-based film or other two-dimensional material, and the highest permeability can be
25 located farther away. Those of skill in the art will understand that permeability of a layer may increase or decrease without pore diameter or porosity changing, e.g., in response to chemical functionalization, applied pressure or other factors.

[0056] In various embodiments, the thickness and structure of the supporting layer can be chosen to convey a desired degree of structural support (*e.g.*, to prevent tearing and/or
30 buckling) to the graphene or graphene-based film or other two-dimensional material

following its removal from a growth substrate. In various embodiments, the supporting layer can have a thickness of about 1 mm or less. In more particular embodiments, a thickness of the supporting layer can range between about 500 nm and about 100 μm , or between about 1 μm and about 50 μm , or between about 1 μm and about 10 μm .

5 [0057] In some embodiments, both the graphene or graphene-based film or other two-dimensional material and the supporting layer can include a plurality of pores therein. When both the two-dimensional material and the supporting layer contain pores, the pores in the two-dimensional material are generally smaller than the pores in the supporting layer. For example, in some embodiments, the supporting layer can contain pores that are about 1 μm in
10 size or larger and the graphene or graphene-based film or other two-dimensional material can contain pores that are about 10 nm in size or smaller. Accordingly, in various embodiments, the sizes or diameters of pores in the graphene or graphene-based film or other two-dimensional material are at least about 10-fold smaller than are the sizes or diameters of pores in the supporting layer, and in other embodiments, the sizes or diameters of pores in the
15 graphene or graphene-based film or other two-dimensional material are at least about 100-fold smaller than are the sizes or diameters of pores in the supporting layer.

[0058] The technique used for introducing a plurality of pores into the graphene or graphene-based film or other two-dimensional material is not considered to be particularly limited and can include various chemical and physical perforation techniques. Suitable
20 perforation techniques can include, for example, particle bombardment, chemical oxidation, lithographic patterning, or any combination thereof. In some embodiments, perforation of the graphene or graphene-based film or other two-dimensional material to produce pores therein can occur in conjunction with establishing pores in the supporting layer. In some or other embodiments, a perforation process can be applied to the graphene or graphene-based film or
25 other two-dimensional material before depositing a supporting layer thereon. In some embodiments, pores can be introduced in the graphene, graphene-based material or other two-dimensional material while it is adhered to its growth substrate. In still other embodiments, the graphene or graphene-based film or other two-dimensional material can be perforated after releasing the graphene or graphene-based film or other two-dimensional material from
30 its growth substrate, such as through etching the growth substrate.

[0059] In various embodiments, the supporting layer can be formed from a porous or permeable polymer or a porous or permeable ceramic material. Suitable techniques for depositing supporting layers formed from these materials are discussed below.

[0060] Porous or permeable polymers can be deposited or formed by various processes used to create membranes for gas separation or microfiltration applications. Suitable techniques for depositing or forming a porous or permeable polymer on the graphene or graphene-based film or other two-dimensional material can include casting or depositing a polymer solution onto the graphene or graphene-based film or other two-dimensional material using a method such as spin-coating, curtain coating, doctor-blading, immersion coating, electrospinning, or other like techniques. Suitable polymers for forming a porous or permeable supporting layer on the graphene or graphene-based film or other two-dimensional material are not believed to be particularly limited and can include, for example, polysulfones, polyethersulfones (PES), polyvinylidene fluoride (PVDF), polypropylene, cellulose acetate, polyethylene, polycarbonate, fluorocarbon polymers such as polytetrafluoroethylene, and mixtures and block co-polymers thereof. Further disclosure regarding these techniques and others follows hereinafter.

[0061] In some embodiments, the process for forming a supporting layer on the graphene or graphene-based film or other two-dimensional material can include an electrospinning process, in which a plurality of polymer filaments are randomly laid down to form a porous mat on the graphene or graphene-based film or other two-dimensional material. The mat can have pores defined therein as the filaments of the supporting layer are deposited. FIGURE 6 shows an illustrative SEM image of a graphene or graphene-based film deposited upon a plurality of electrospun PVDF fibers. The electrospinning process can constitute a wet electrospinning process in some embodiments or a dry electrospinning process in other embodiments. In dry electrospinning processes, the spun fibers of the supporting layer can remain as essentially discrete entities once deposited. In contrast, wet electrospinning processes can deposit the spun fibers such that they are at least partially fused together when deposited. Accordingly, considerable flexibility can be realized in the size and morphology of the fiber mat deposited by an electrospinning process. These factors can impact the degree of porosity and the effective pore size of the supporting layer. The thickness of the supporting layer can also impact the effective porosity. In some

embodiments, electrospinning processes can be adapted to produce gradient porosity in the supporting layer, as discussed above. The porosity of the supporting layer can include effective porosity values up to about 95% with a broad range of pore sizes. In some embodiments, a single spinneret can be moved to lay down a mat of the supporting layer. In other embodiments, multiple spinnerets can be used for this purpose. In some embodiments, the spun fibers in an electrospun supporting layer can have a fiber diameter ranging between about 10 nm and about 1 μ m, or between about 10 nm and about 500 nm, or between about 20 nm and about 100 nm. Although the effective pore size can be large and variable in electrospun fiber supporting layers, the fibers can still readily provide mechanical stabilization to the graphene or graphene-based film or other two-dimensional material following release from its growth substrate.

[0062] In some embodiments, the supporting layer can be deposited by a solution-coating process onto the graphene or graphene-based film or other two-dimensional material, particularly for a polymer film supporting layer. Illustrative solution-coating processes can include dip coating processes, spin coating processes, spray coating processes, the like, and any combination thereof. A sacrificial material can be included in the coating solution or can be co-deposited with the coating solution so that the sacrificial material is present in the as-deposited polymer film. The sacrificial material can constitute a degradable material, removable material or a dissolvable material that is degraded, removed or dissolved after depositing the supporting layer in order to introduce a plurality of pores therein. As used herein, the term "degradable" refers to both chemical and physical degradation processes, such as chemical breakdown, melting and the like. The size of the sacrificial material can be chosen to produce pores having a desired size within the supporting layer upon removal of the sacrificial material. In general, any sacrificial material can be used provided that its degradation, removal or dissolution does not also remove or substantially damage the material of the supporting layer. Illustrative sacrificial materials can include, for example, soluble salts, soluble organic compounds, degradable polymer particulates, waxes, low melting alloys, and the like. In some embodiments of this approach, the pores within the supporting layer can be opened while the graphene or graphene-based film or other two-dimensional material is adhered to its growth substrate. In other embodiments, the pores can be opened after or concurrently with release of the graphene, graphene-based material or

other two-dimensional material from its growth substrate. Accordingly, in various embodiments, solvent exchange or thermal annealing processes can be used to open the pores in the supporting layer. Dissolution-based processes for defining pores in the supporting layer are believed to be more easily conducted than are complete removal of a sacrificial supporting layer, because an easily dissolvable, removable or degradable material can be included within a more robust supporting layer material.

[0063] In alternative embodiments, a sacrificial material can be deposited on the surface of the graphene or graphene-based film or other two-dimensional material before solution-phase deposition of the supporting layer. So long as the thickness of the deposited layer is such that the sacrificial material remains accessible, a plurality of pores can be defined in the supporting layer. For example, the thickness of the supporting layer can be adjusted to be smaller than an effective diameter of the sacrificial material such that pores are defined in the supporting layer upon removal of the sacrificial material.

[0064] In still other alternative embodiments for forming a supporting layer, non-degradable particulates can be co-deposited with a polymer in order to increase the fractional free volume between polymer chains. By increasing the fractional free volume, the effective permeability of the supporting layer can be increased by establishing a solution-diffusion layer but without defining discrete pores. An illustrative example of such supporting layers include those formed from NAFION (a sulfonated tetrafluoroethylene copolymer, which is selectively permeable toward movement of cations). Such supporting layers can still be desirable for use in conjunction with a perforated graphene or graphene-based film or other perforated two-dimensional material according to the various embodiments of the present disclosure.

[0065] Still other processes can be used for depositing the supporting layer in porous or permeable form upon the graphene or graphene-based film or other two-dimensional material. Particularly for non-polymeric supporting layers. In some embodiments, atomic layer deposition (ALD), chemical vapor deposition (CVD), physical vapor deposition (PVD) or other known deposition techniques can be used to deposit a porous or permeable supporting layer formed from a ceramic material. For example, an alumina porous or permeable supporting layer can be formed by ALD. A porous or permeable supporting layer

deposited by ALD can have up to about 200 individual layers and can range from about 10 nm to about 20 nm in thickness. In some embodiments, a sacrificial material, such as those discussed above, can be used to introduce a plurality of pores into a supporting layer deposited by ALD.

5 [0066] In still other embodiments, various lithographic techniques can be used to pattern a plurality of pores in an existing supporting layer that is originally substantially non-porous. Patterning can be ordered or random in nature. Suitable lithographic techniques will be familiar to one having ordinary skill in the art. When conducted following removal of the two-dimensional material from the growth substrate, lithographic generation of pores in the
10 supporting layer can be conducted from the top-side or bottom-side of the graphene or graphene-based film (*e.g.*, see FIGURE 2). Top-side generation of pores in the supporting layer can also introduce a plurality of pores of like size in the two-dimensional material if the penetration depth is sufficiently great, or pores can be generated in the supporting layer only if the penetration depth is not sufficient to break through the two-dimensional material.
15 Bottom-side generation of pores in the supporting layer, in contrast, can result in pore generation in both the two-dimensional material and the supporting layer, since the lithographic beam necessarily traverses the two-dimensional material in the course of penetrating the supporting layer.

[0067] In still other embodiments, the supporting layer can include a perforated
20 graphene, graphene-based material or other perforated two-dimensional material having pores that are larger than those in the perforated graphene, graphene-based material or other perforated two-dimensional material onto which the supporting layer is deposited. In a specific example, a lithographic mask can be applied to graphene or graphene-based material on its growth substrate, and a plurality of large perforations (*e.g.*, about 100 nm in size or
25 larger) can be densely defined in the graphene or graphene-based material. Thereafter, the lithographic mask can be left on the graphene or graphene-based material and the growth substrate can be removed, thereby providing perforated graphene or graphene-based material supported by the lithographic mask. The perforated graphene or graphene-based material supported by the lithographic mask can then be contacted graphene surface-to-graphene
30 surface in order to define a hybrid supporting layer for the graphene or graphene-based material containing smaller pores. Through van der Waals forces, good adhesion can occur

between the two graphene or graphene-based material surfaces. Upon removal of the growth substrate from the perforated graphene or graphene-based material containing smaller pores, the lithographic mask can provide mechanical support to the composite structure as described herein.

5 [0068] In some embodiments, the supporting layer, the secondary substrate (if present), or both can be functionalized. Specifically, the supporting layer and/or the secondary substrate can bear functionality that increases the compatibility and degree of adhesion to the graphene or graphene-based film or other two-dimensional material. In some
10 embodiments, the supporting layer and/or the secondary substrate can bear functional groups that promote covalent bond formation to functional groups in the graphene or graphene-based film or other two-dimensional material. Residual functional groups present in graphene or graphene-based material can include, for example, carboxylic acids, alcohols, epoxides, carbonyls, and the like. Accordingly, covalent bond formation to the graphene or graphene-based material can involve the formation of moieties such as, for example, esters, ethers,
15 aldehydes, alcohols, amides, carbonyl addition compounds, epoxide addition compounds, and the like.

[0069] Accordingly, in some embodiments, processes described herein can include providing a graphene or graphene-based film adhered to a growth substrate, perforating the film to introduce a plurality of pores therein, depositing a supporting layer on the film while
20 the film is adhered to the growth substrate, and releasing the film from the growth substrate. The graphene or graphene-based film remains in contact with the supporting layer following release of the film from the growth substrate. The growth substrate may comprise a metal. The supporting layer also may comprise a plurality of pores.

[0070] In some embodiments, the processes described herein can include performing
25 a filtration operation with a composite structure containing a graphene or graphene-based film and the supporting layer. The filtration operation can include ultrafiltration, microfiltration, nanofiltration, molecular filtration, reverse osmosis or any combination thereof. The material being filtered by the perforated graphene or graphene-based material can constitute any material that allows the desired filtrate to pass through the pores within the
30 perforated graphene or graphene-based material while retaining the bulk material on an

opposite side of the graphene or graphene-based material. Materials that can be filtered using graphene or graphene-based materials comprising nanometer or subnanometer-sized pores include, for example, ions, small molecules, viruses, proteins, and the like. In some embodiments, the supported graphene or graphene-based material described herein can be
5 used in water desalination, gap-phase separation or water purification applications.

[0071] Accordingly, in various embodiments, the combination of a perforated graphene or graphene-based material and a supporting layer, optionally in combination with a porous or permeable secondary substrate, can constitute at least a portion of a filtration membrane. Illustrative configurations for a filtration membrane containing perforated
10 graphene or graphene-based material and a supporting layer containing pores are depicted in the FIGURES herein.

[0072] Although the invention has been described with reference to the disclosed embodiments, those skilled in the art will readily appreciate that these are only illustrative of the invention. It should be understood that various modifications can be made without
15 departing from the spirit of the invention. The invention can be modified to incorporate any number of variations, alterations, substitutions or equivalent arrangements not heretofore described, but which are commensurate with the spirit and scope of the invention. Additionally, while various embodiments of the invention have been described, it is to be understood that aspects of the invention may include only some of the described embodiments. Accordingly,
20 the invention is not to be seen as limited by the foregoing description.

[0073] Every formulation or combination of components described or exemplified can be used to practice the invention, unless otherwise stated. Specific names of compounds are intended to be exemplary, as it is known that one of ordinary skill in the art can name the same compounds differently. When a compound is described herein such that a particular
25 isomer or enantiomer of the compound is not specified, for example, in a formula or in a chemical name, that description is intended to include each isomer and enantiomer of the compound described individually or in any combination. One of ordinary skill in the art will appreciate that methods, device elements, starting materials and synthetic methods other than those specifically exemplified can be employed in the practice of the invention without resort
30 to undue experimentation. All art-known functional equivalents, of any such methods,

device elements, starting materials and synthetic methods are intended to be included in this invention.

[0074] Whenever a range is given in the specification, for example, a temperature range, a time range, or a composition range, all intermediate ranges and subranges, as well as
5 all individual values included in the ranges given are intended to be included in the disclosure. When a Markush group or other grouping is used herein, all individual members of the group and all combinations and subcombinations possible of the group are intended to be individually included in the disclosure.

[0075] As used herein, "comprising" is synonymous with "including," "containing,"
10 or "characterized by," and is inclusive or open-ended and does not exclude additional, unrecited elements or method steps. As used herein, "consisting of" excludes any element, step, or ingredient not specified in the claim element. As used herein, "consisting essentially of" does not exclude materials or steps that do not materially affect the basic and novel characteristics of the claim. Any recitation herein of the term "comprising", particularly in a
15 description of components of a composition or in a description of elements of a device, is understood to encompass those compositions and methods consisting essentially of and consisting of the recited components or elements. The invention illustratively described herein suitably may be practiced in the absence of any element or elements, limitation or limitations which is not specifically disclosed herein.

20 [0076] The terms and expressions which have been employed are used as terms of description and not of limitation, and there is no intention in the use of such terms and expressions of excluding any equivalents of the features shown and described or portions thereof, but it is recognized that various modifications are possible within the scope of the invention claimed. Thus, it should be understood that although the present invention has
25 been specifically disclosed by preferred embodiments and optional features, modification and variation of the concepts herein disclosed may be resorted to by those skilled in the art, and that such modifications and variations are considered to be within the scope of this invention as defined by the appended claims.

[0077] In general the terms and phrases used herein have their art-recognized
30 meaning, which can be found by reference to standard texts, journal references and contexts

known to those skilled in the art. The preceding definitions are provided to clarify their specific use in the context of the invention.

[0078] All references throughout this application, for example patent documents including issued or granted patents or equivalents; patent application publications; and non-
5 patent literature documents or other source material; are hereby incorporated by reference herein in their entireties, as though individually incorporated by reference, to the extent each reference is at least partially not inconsistent with the disclosure in this application (for example, a reference that is partially inconsistent is incorporated by reference except for the partially inconsistent portion of the reference).

10 [0079] All patents and publications mentioned in the specification are indicative of the levels of skill of those skilled in the art to which the invention pertains. References cited herein are incorporated by reference herein in their entirety to indicate the state of the art, in some cases as of their filing date, and it is intended that this information can be employed herein, if needed, to exclude (for example, to disclaim) specific embodiments that are in the
15 prior art. For example, when a compound is claimed, it should be understood that compounds known in the prior art, including certain compounds disclosed in the references disclosed herein (particularly in referenced patent documents), are not intended to be included in the claims.

CLAIMS

What is claimed is the following:

1. A process comprising:
 - providing a two-dimensional material adhered to a growth substrate;
 - 5 depositing a supporting layer on the two-dimensional material while the two-dimensional material is adhered to the growth substrate; and
 - releasing the two-dimensional material from the growth substrate, the two-dimensional material remaining in contact with the supporting layer following release of the two-dimensional material from the growth substrate.
- 10 2. The process of claim 1, wherein releasing the two-dimensional material from the growth substrate comprises etching the growth substrate.
3. The process of claim 1, wherein the two-dimensional material comprises a graphene or graphene-based film, a transition metal dichalcogenide, α -boron nitride, silicene, germanene or a combination thereof.
- 15 4. The process of claim 1, wherein the supporting layer has a thickness of 1 mm or less.
5. The process of claim 1, further comprising:
 - introducing a plurality of pores into the supporting layer.
6. The process of claim 5, wherein the supporting layer comprises a plurality of polymer filaments formed on the two-dimensional material by a wet electrospinning process or a
- 20 dry electrospinning process, the plurality of pores in the supporting layer being introduced as the supporting layer is deposited.
7. The process of claim 5, wherein the supporting layer comprises a polymer film coated on the two-dimensional material, the polymer film further comprising a sacrificial material that is degraded, removed or dissolved after depositing the supporting layer to introduce

the plurality of pores in the supporting layer.

8. The process of claim 5, wherein the supporting layer has a porosity gradient throughout its thickness.

9. The process of claim 5, wherein the supporting layer comprises a ceramic material deposited by atomic layer deposition.

10. The process of claim 5, further comprising:

perforating the two-dimensional material to introduce a plurality of pores therein, the plurality of pores in the two-dimensional material being at least 10-fold smaller than the plurality of pores in the supporting layer.

11. The process of claim 10, wherein the two-dimensional material is perforated before depositing the supporting layer thereon.

12. The process of claim 10, wherein the two-dimensional material is perforated after releasing the two-dimensional material from the growth substrate.

13. The process of claim 10, further comprising:

transferring the two-dimensional material and the supporting layer to a secondary substrate.

14. The process of claim 1, further comprising:

perforating the two-dimensional material to introduce a plurality of pores therein.

15. A process comprising:

providing a graphene or graphene-based film adhered to a growth substrate, the growth substrate comprising a metal;

perforating the graphene or graphene-based film to introduce a plurality of pores therein;

depositing a supporting layer on the graphene or graphene-based film while the

graphene or graphene-based film is adhered to the growth substrate, the supporting layer also comprising a plurality of pores; and

releasing the graphene or graphene-based film from the growth substrate, the graphene or graphene-based film remaining in contact with the supporting layer following release of the film from the growth substrate.

16. The process of claim 15, wherein releasing the graphene or graphene-based film from the growth substrate comprises etching the growth substrate.

17. The process of claim 16, wherein etching the growth substrate comprises at least partially dissolving the metal with an etch solution.

18. The process of claim 15, wherein the graphene or graphene-based film is perforated before depositing the supporting layer thereon.

19. The process of claim 15, wherein the graphene or graphene-based film is perforated after releasing the graphene or graphene-based film from the growth substrate.

20. The process of claim 15, wherein the plurality of pores in the graphene or graphene-based film are at least 10-fold smaller than the plurality of pores in the supporting layer.

21. The process of claim 15, wherein the supporting layer has a thickness of 1 mm or less.

22. The process of claim 15, further comprising:

transferring the graphene or graphene-based film and the supporting layer to a secondary substrate.

23. The process of claim 22, wherein the secondary substrate contains a plurality of pores.

24. The process of claim 22, wherein the graphene or graphene-based film is sandwiched between the secondary substrate and the supporting layer.

25. The process of claim 15, wherein the supporting layer comprises a porous or permeable

polymer or a porous or permeable ceramic material.

26. A filtration membrane comprising a perforated graphene or graphene-based material and a supporting layer, the filtration membrane being prepared by the process of claim 15.